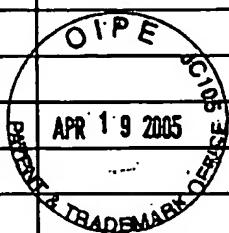


SUBSTITUTE FORM PTO-1449 (MODIFIED)		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY. DOCKET NO. BEET/09	SERIAL NO. 10/524,525
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(37 CFR 1.98(b))					

## U.S. PATENT DOCUMENTS

EXAMINER INITIAL		PATENT NUMBER	ISSUE DATE	PATENTEE	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
	A.A						
	A.B						
	A.C						
	A.D						
	A.E			APR 19 2005			
	A.F						
	A.G						
	A.H						
	A.I						
	A.J						
	A.K						



## FOREIGN PATENTS OR PUBLISHED FOREIGN PATENT APPLICATIONS

		DOCUMENT NUMBER	PUBLICATION DATE	COUNTRY OR PATENT OFFICE	CLASS	SUBCLASS	TRANSLATION (YES/NO)
/SA/	A.L	KR 2002041363A	06/2002	Republic of Korea	H01L	21/3065	No
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	A.N						
	A.O						
	A.P						
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/SA/	A.R	Ayon et al., <u>Characterization of a Time Multiplexed Inductively Coupled Plasma Etcher</u> , Journal of the Electrochemical Society, January 1999, Vol. 146, Issue 1, pp. 339-349
/SA/	A.S	The International Bureau of WIPO, <u>English Translation of the International Preliminary Examination Report</u> , November 17, 2004 (12 pages)
	A.T	

EXAMINER	DATE CONSIDERED
/Shamim Ahmed/ (04/11/2007)	04/11/2007

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		INFORMATION DISCLOSURE STATEMENT BY APPLICANT						APPLICANT Martin Hausner	
		(Use several sheets if necessary)						FILING DATE February 11, 2005	GROUP Unknown
(37 CFR 1.98(b))									

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EXAMINER INITIAL		PATENT NUMBER						ISSUE DATE	PATENTEE	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
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	A.J											
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		DOCUMENT NUMBER	PUBLICATION DATE	COUNTRY OR PATENT OFFICE	CLASS	SUBCLASS	TRANSLATION (YES/NO)
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